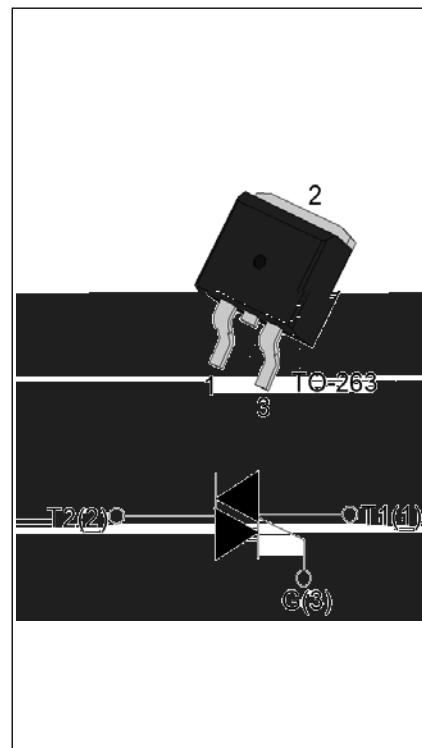


**DESCRIPTION:**

The T1650H-8E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T1650H-8E provides a very high switching capability up to junction temperatures of 150°C. Package TO-263 is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	50/50/50	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-150	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	800	V
RMS on-state current ($T_c = 0.125^\circ C$)	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	160	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^\circ C$)		176	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	128	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=150^\circ C$)	di/dt	100	A/s
Peak gate current ($t_p=20\mu s$, $T_j=150^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150^\circ C$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage ($T_j=25^\circ C$; non-repetitive, off-state; FIG.8)	V_{pp}	4	kV
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ELECTRICAL CHARACTERISTICS (ST_{SS} unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=150^\circ C$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	80	mA
I_H				100	
dV/dt	$V_D=540V$ Gate Open $T_j=150^\circ C$		MIN.	1800	V/s
$(dI/dt)c$	G 9 G W F $\downarrow 150V$ 7		MIN.	25	A/ms
t_{on}	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25^\circ C$	TYP.	12	s	
t_{off}			80		

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=22.5A t_p=380\mu s$	$T_j=25^\circ C$	1.4	V
V_{TO}	Threshold voltage	$T_j=150^\circ C$	0.75	V
R_D	Dynamic resistance	$T_j=150^\circ C$	27	P
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ C$	5	A
I_{RRM}		$T_j=150^\circ C$	2	mA

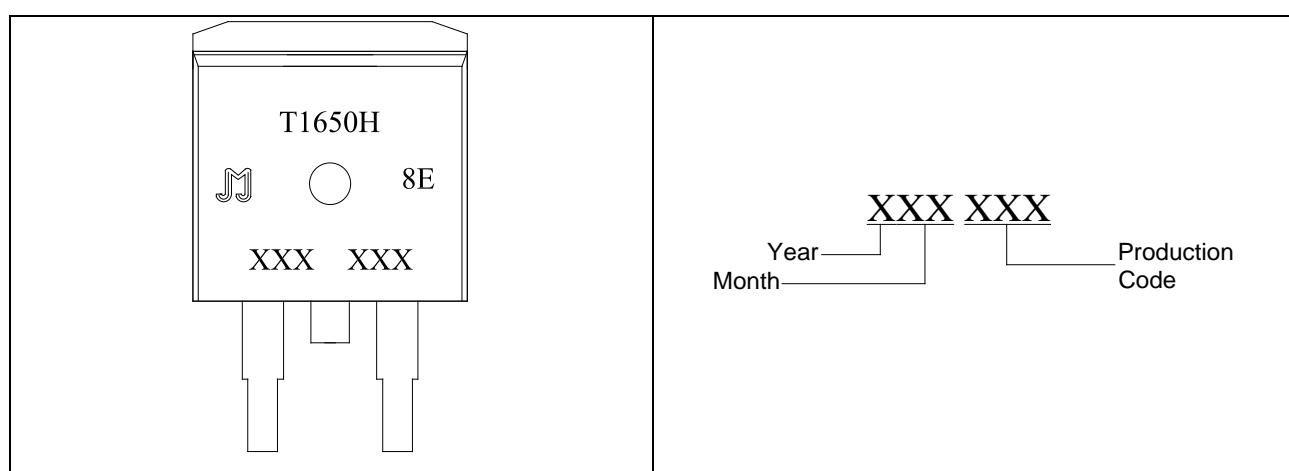
THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.2	/W
$R_{th(j-a)}$	junction to ambient (AC)	45	/W

ORDERING INFORMATION

T	16	50	H	-8	E	-/
Triacs						Blank:Tube -TR:Tape & Reel
	<u>I_{T(RMS)}:16A</u>					
		<u>50:I_{GT1-3} 050 mA</u>				
				<u>8:V_{DRM} /V_{RRM} 1800 V</u>		
					<u>High junction temperature</u>	

MARKING



T1650H-8E



FIG.1 Maximum power dissipation versus RMS on-state current

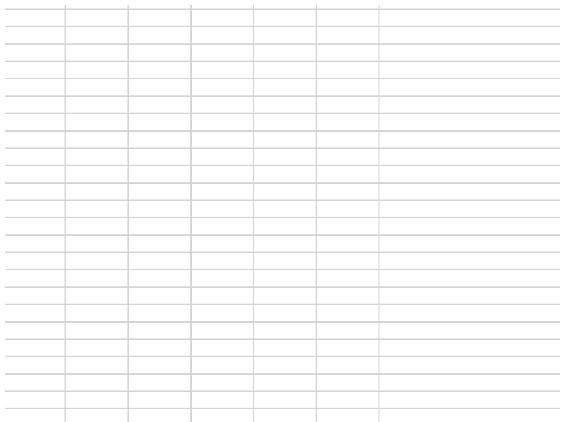


FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

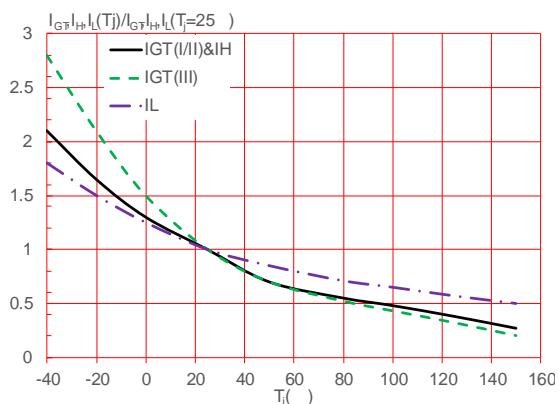
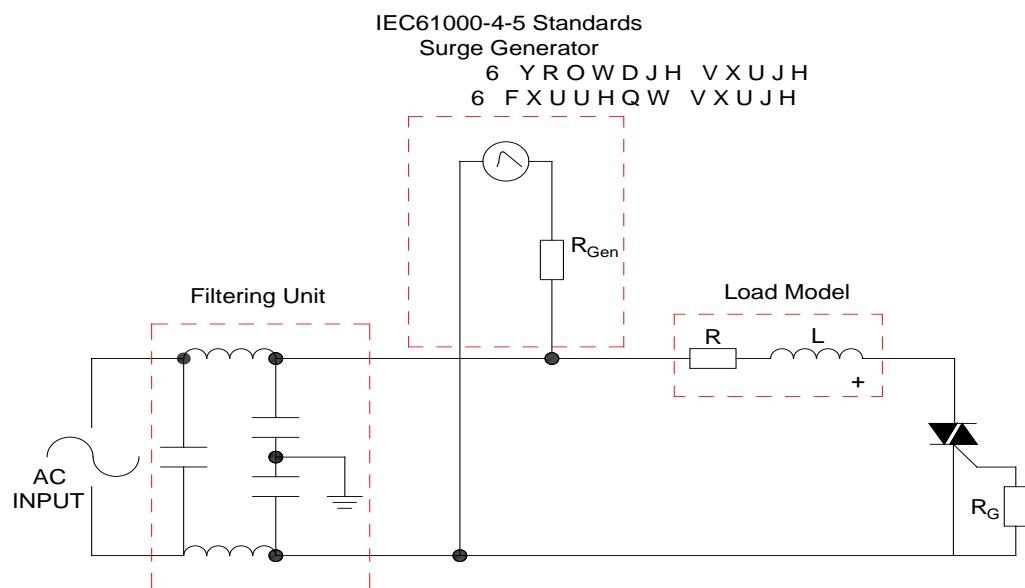
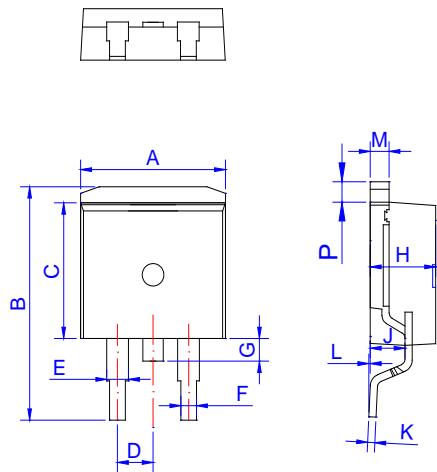


FIG.8 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



T1650H-8E

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.37		0.378
D	2.40		2.70	0.094		0.106
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033
G	1.00		1.50	0.039		0.059
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053
P	1.20		1.50	0.047		0.059

FOOTPRINT

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